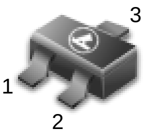
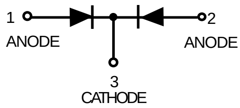
SCHOTTKY BARRIER DIODE

LRB715T1



SC−70/SOT−323



●Features

Small surface mounting type SC-70/SOT323

Low V_F and low I_R

High reliability

●Construction

silicon epitaxial planar

MAXIMUM RATINGS ($T_A = 25°C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+150	°C

DEVICE MARKING

LRB715T1=3D

ELECTRICAL CHARACTERISTICS($T_A = 25°C$)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.37	V	I_F=1mA
Reverse current	I_R	–	–	1	μV	V_R=10V
Capacitance between terminals	C_T	–	–	–	V	V_R=1V,f=1MHz

Electrical characteristic curves(T_A = 25°C)

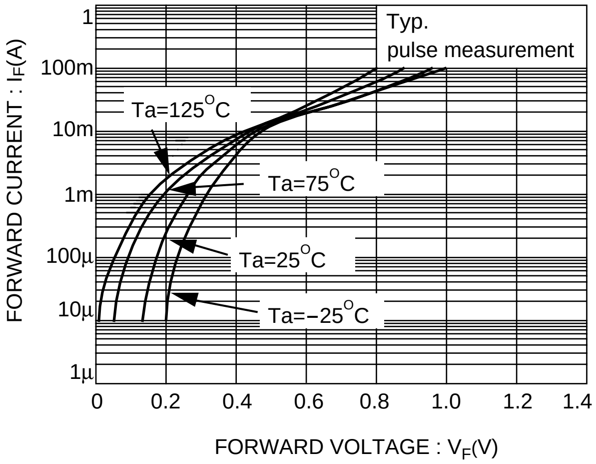


Fig. 1 Forward characteristics

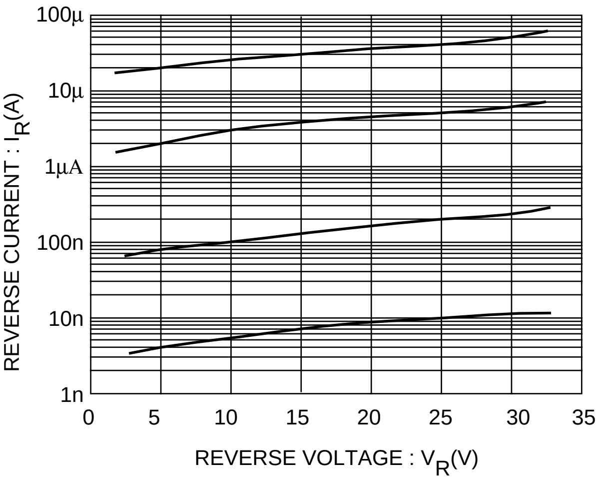


Fig. 2 Reverse characteristics

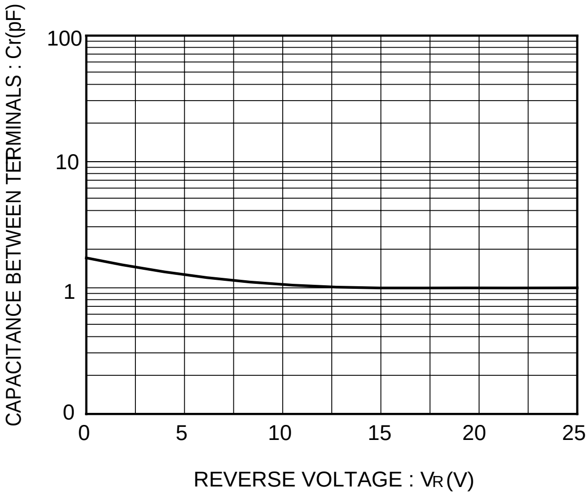


Fig. 3 Capacitance between terminals characteristics

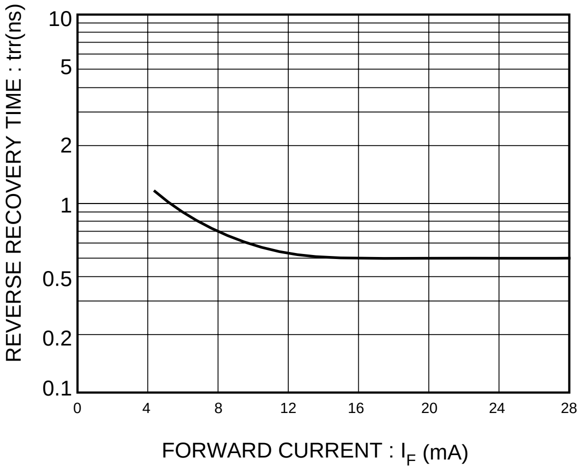
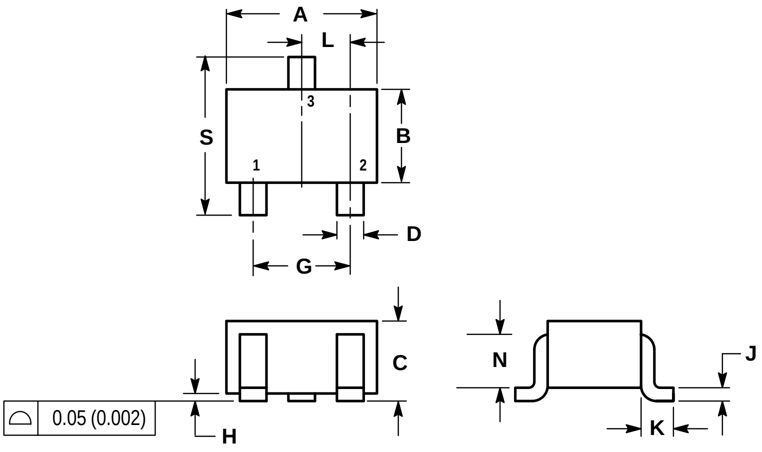


Fig. 4 Reverse recovery time characteristics

SC–70/SOT–323



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017REF		0.425REF	
L	0.026BSC		0.650BSC	
N	0.028REF		0.700REF	
S	0.079	0.095	2.00	2.40

PIN 1. ANODE
2. ANODE
3. CATHODE